

November 1986

Interfacing the 8207 Advanced Dynamic RAM Controller to the iAPX 286

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INTRODUCTION

The 80286 high speed microprocessor pushes microprocessor based systems to new performance levels. However, its high speed bus requires special design considerations to utilize that performance. Interfacing the 80286 to a dynamic RAM array require many timings to be analyzed, refresh cycle effects on bus timing examined, minimum and maximum signal widths noted, and the list continues.

The 8207 Advanced Dynamic RAM Controller was specifically designed to solve all interfacing issues for the 80286, provide complete control and timing for the DRAM array, plus achieve optimum system performance. This includes the normal RAM 8 warmup cycles, various refresh cycles and frequencies, address multiplexing, and address strobe timings. The 8207 Dynamic RAM Controller's system interface and RAM timing and control are programmable to permit it to be used in most applications.

Integrating these functions (plus dual port and error correcting interfaces) allows the user to realize significant savings in both engineering design time, PC board space and product cost. For example, in comparing the 8207 to the ISBC012B 512k byte RAM board (where the DRAM timing and control is done entirely with TTL), the 8207 design saved board space (3 in² vs 10 in²); used less power (420 mA vs 1220 mA); reduced the design time; and increased margins due to less skewing of timings. The comparison is based upon a single port 8207 design and does not include its RAM warm-up, dual port, error correcting, and error scrubbing or RAM interleaving features.

This Application Note will detail an 80286 and 8207 design. The reader should have read the 8207 and the 80286 data sheets, a DRAM data sheet*, and have them available for reference.

DESIGN GOALS

The main objective of this design is to run the RAM array without wait states, to maximize the 80286's performance, and to use as little board space as possible. The 80286 will interface synchronously to Port A of the 8207 and the 8207 will control 512k bytes of RAM (4 banks using 64k DRAMs). The dual port and error correcting features of the 8207 are covered in separate Application Notes.

*All RAM references in this Application Note are based upon Intel's CMOS 51C84-12 64k Dynamic RAM. Any DRAM with similar timings will function. Refer to section 4.4.

8207 INTERFACE

The 8207 Memory design can be subdivided into three sections:

- Programming the 8207.
- The 80286/8207 interface.
- The Dynamic RAM array.

Programming the 8207

The RAM timing is configured via the 16 bit program word that the 8207 shifts-in when reset. This can require two 74LS165 shift registers to provide complete DRAM configurability. The 8207 defaults to the configuration shown in Table 1 when PDI is connected to ground. This design does not need the flexibility the shift registers would allow since standard 8207/80286 clock frequencies, DRAM speeds and refresh rates are used. Table 1 details the 8207/80286 configuration and Table 10 in the Data Sheet identifies "CO" as the configuration of the 8207 all timings will be referenced to (80286 mode at 16 MHz using fast RAMs = CO).

**Table 1. Default Non-ECC Programming,
PD1 Pin (57) Tied to Ground**

Port A is Synchronous (EAACKA and XACKA)
Port B is Asynchronous (LAACKB and XACKB)
Fast-cycle Processor Interface (10 or 16 MHz)
Fast RAM 100/120 ns RAM
Refresh Interval uses 236 clocks
128 Row refresh in 2 ms; 256 Row refresh in 4 ms
Fast Processor Clock Frequency (16 MHz)
"Most Recently Used" Priority Scheme
4 RAM banks occupied

The 8207 will accept 80286 status inputs when the PCTLA pin is sampled low at reset. This pin is not necessary for an 80286 design (besides programming) and is tied to ground.

Refresh is the final option to be programmed. If the Refresh pin is sampled high at reset, an internal timer

is enabled, and if low at reset, this timer is disabled. The first method is the easiest to implement, so the RFRQ pin is tied to VCC.

The differential reset circuit shown in the Data Sheet is necessary only to ensure that memory commands are not received by the 8207 when Port A is changed from synchronous to asynchronous (vice versa for Port B). This design keeps Port A synchronous so no differential reset circuit is needed.

RAM Array

The 8207 completely controls all RAM timings, warm-up cycles, and refresh cycles. To determine if a particular RAM will work with the 8207, calculate the margins provided by the 8207 (Table 15, 16—8207 Data Sheet) and ensure they are greater than the RAM requirement. An additional consideration is the access times of the RAMs. The access time of the system is dependent upon the number of data buffers between the 80286 and the DRAMs. To operate the 80286 at zero wait states requires access times of 100–120 ns. Slower RAMs can be used (150 ns) by either adding a wait state (programming the 8207 for “C1”) or reducing the clock frequency (to 14.9 MHz approximately and maintaining the CO configuration).

All write cycles are “late writes” and the data out lines of the RAM will go active. This will require separate data in and out lines in the RAM array. Another consideration for the RAM array is the proper layout of the RAM, and impedance matching resistors on the 8207 outputs. Proper layout is covered in Intel's RAM Data Sheets and Application Notes.

Microprocessor Array

To achieve no wait state operation, the 8207's clock input must be connected to the 80286's clock input. The EAACK (early acknowledge) output of the 8207 must connect to the SRDY input of the 82284. The 8207's address inputs connect directly to the 80286 address outputs and the addresses are latched internally. This latch is strobed by an internal signal with the same timing as LEN (which is for dual port 80286 designs). Figure 2 shows the timing relationship between LEN and the 80286.

LEN will fall from high to low, which latches the bus address internally, when a valid command is received. LEN can go high in two clock cycles if the RAM cycle started (RAS going low) at the same time LEN went low. If the 8207 is doing a refresh cycle, the 80286 will be put into wait states until the memory cycle can start.

LEN will then go high two clocks after RAS starts, since addresses are no longer needed for the current RAM cycle. Thus the low period of LEN could be much longer than listed in the Data Sheet.

DESIGNING THE HARDWARE

Figure 1 shows a detailed block diagram of the design and Figure 2 shows the timing relationship between the 8207 and the 80286.

The following analysis of six parameters will confirm that the design will work. These six system parameters are generally considered the most important in any microprocessor—Dynamic RAM design.

8207 Command Setup Margin

Two events must occur for the 8207 to start a memory cycle. Either RD or WR active (low) and PE must be low when the 8207 samples these pins on a falling clock edge. If PE is not valid at the same clock edge that samples RD or WR active, the memory cycle will be aborted and no acknowledge will be issued.

The command setup time is based upon the status being valid at the first falling clock edge.

80286 status valid to 8207 falling clock — 80286 status from clock delay — 8207 command setup to clock ≤ 0

$TCLCL - 80286\ t12\ (max) - 8207\ TKVCL\ (min) \leq 0$

$62.5 - 40\ ns - 20\ ns = 2.5\ ns$

PE is decoded from the address bus and must be set up to the same falling clock edge that recognizes the RD, WR inputs. This margin is determined from the clock edge that issues the address and the clock edge that will recognize RD or WR, minus decoding logic delays.

There are 2 clocks between addresses being issued by the 80286 and PE being sampled by the 8207. Then the 80286 address delay from the clock edge and decoding logic delays are subtracted from this interval. This margin must be greater than 0.

$2TCLCL - 80286\ t13\ (max) - 8207\ TPEVCL\ (min) \leq 0$

$125 - 60 - 30 = 35\ ns$

The address decode logic must use no more than 35 ns (and less is better). Figure 3 shows an easy implementation which uses a maximum of 12 ns.

The 8207 requires a zero ns hold time and is always met.

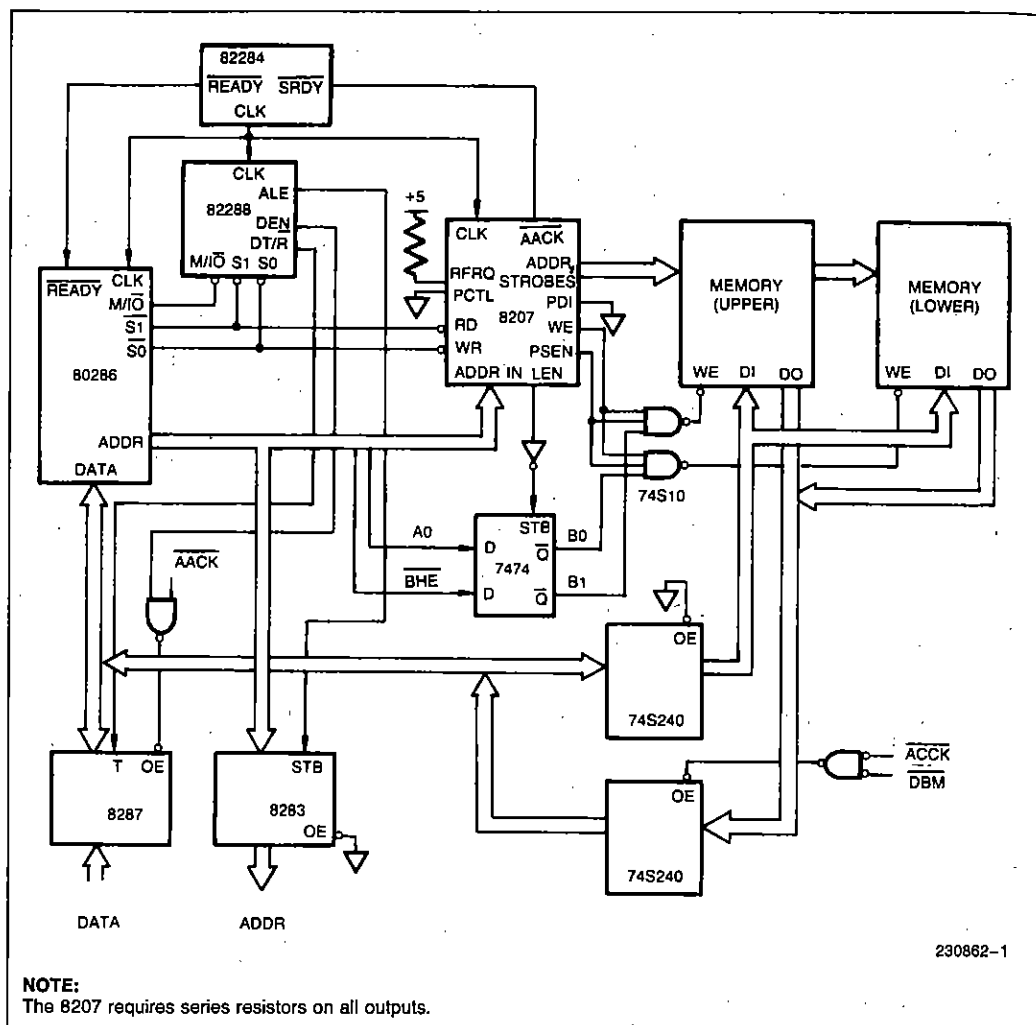


Figure 1. 80286 to 8207, non-ECC, Synchronous System Single Port

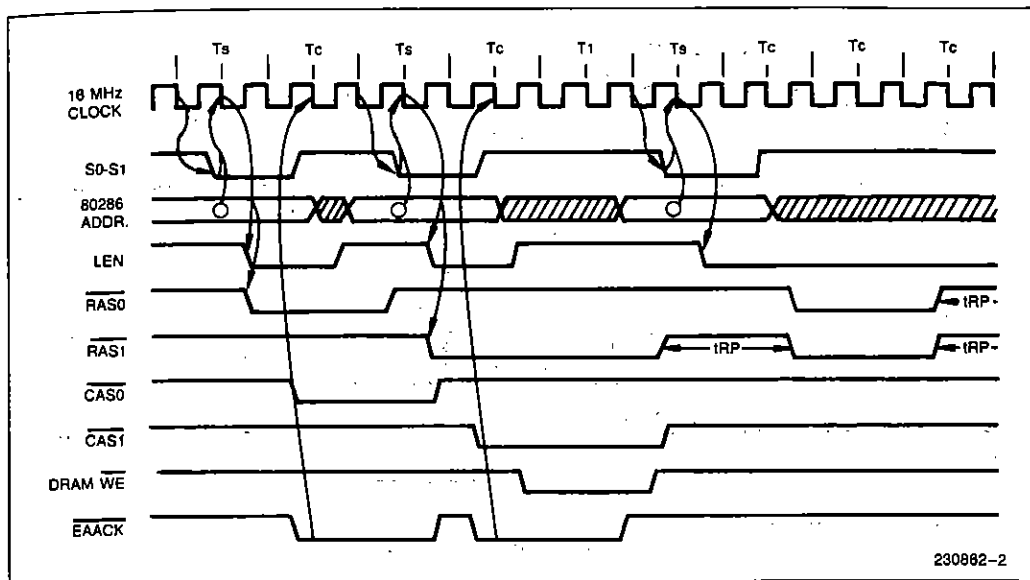


Figure 2. 80286/8207 Timing—"CO"

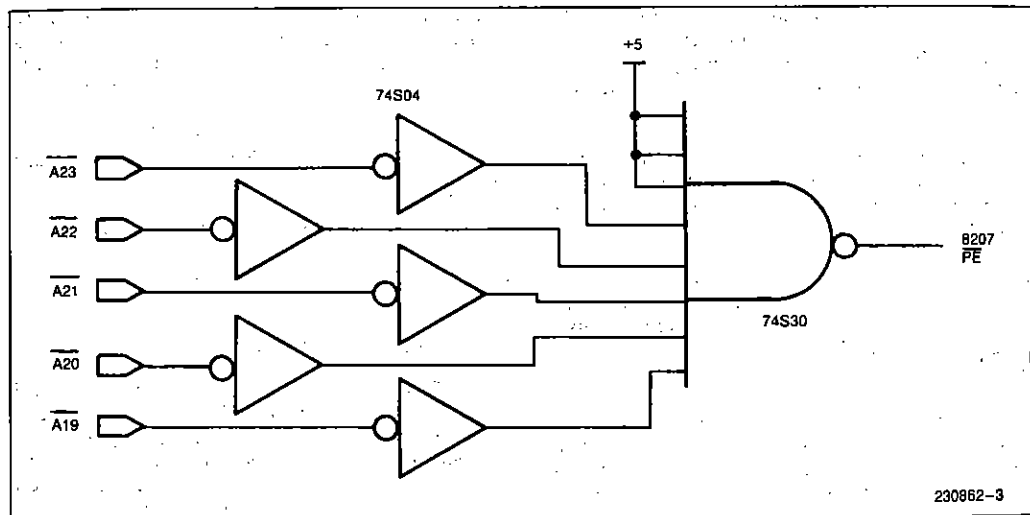


Figure 3. Address Decode Logic

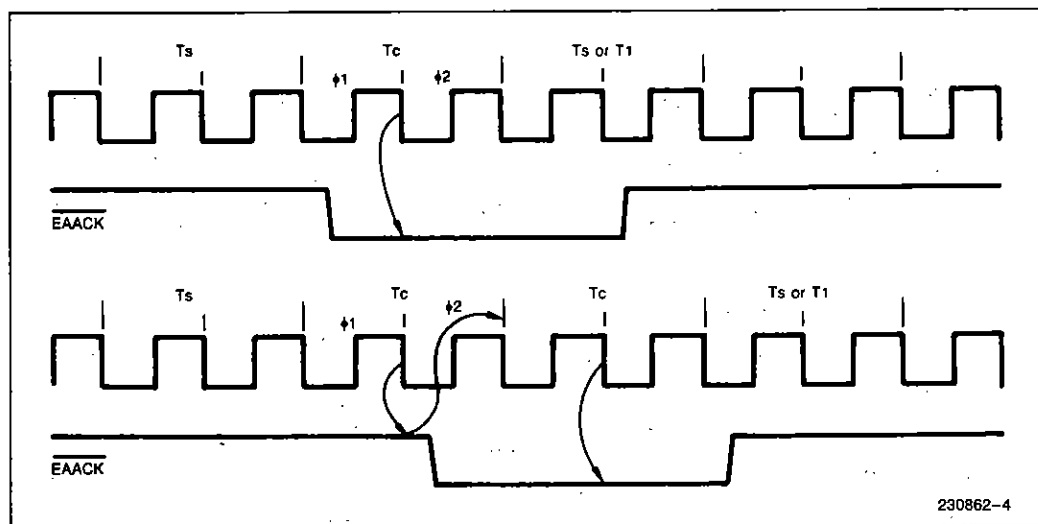


Figure 4. Acknowledge to the 82284

Address Setup Margin

The 8207 must have stable addresses up to two clocks after RAS goes active. This is of no concern to the user, since LEN latches the address internally and will not admit a new address until two clocks after RAS goes active.

Addresses must be stable at least 35 ns (t_{AVCL}) before RAS goes active to allow for propagation delays through the 8207, if a RAM cycle is not delayed by the 8207.

t_{ASR} is a RAM specification. If it is greater than zero, t_{ASR} must be added to the address setup time of the 8207. Address setup is the interval between addresses being issued, by the 80286, and RAS going active, minus appropriate delays.

The margin is determined from the number of clocks between addresses being issued from the 80286 to RAS going active. Exactly when RAS goes active is unimportant, since here we are only interested in the clock edge.

$$2TCLCL - 80286\ t13\ (\max) - 8207\ TAVCL\ (\min) \leq 0$$

$$125\ ns - 60\ ns - 35\ ns = 30\ ns$$

Acknowledge Setup Margin

The 8207 acknowledge (EAACK) can be issued at any point in the 80286 bus cycle (end of $\phi 1$ or $\phi 2$ of T_s or T_c). If EAACK is issued at the end of $\phi 2$ (T_s or T_c), the 80286 will complete the current bus cycle. If

EAACK is issued at the end of $\phi 1$ of T_c , the 82284 will not generate READY to the 80286 in time to end the current bus cycle. A new T_c would then be generated and EAACK would now be sampled in time to terminate the bus cycle. EAACK is 3 clocks long in order to meet setup and hold times for either condition.

We need the margin between the 8207 issuing EAACK and the 82284 needing it. Figure 4 shows a worst case example.

$$TCLCL - 8207\ TCLAKL\ \max - 82284\ t11 \leq 0$$

$$62.5\ ns - 35\ ns - 15\ ns = 12.5\ ns$$

Read Access Margin

The 8207 will typically start a memory cycle (i.e. RAS goes low) at the end of $\phi 1$ of T_s . But if the start of a memory cycle is delayed (by a refresh cycle for instance), then RAS will be delayed. In the first case, this represents 3 clocks and the second case could require 4 clocks to meet the data setup requirements of the 80286. In either case, data must be valid at the end of T_c . The 8207 holds CAS active long enough to ensure valid data is received by the 80286 in either case.

DRAMs specify two access times, RAS access (t_{RAC}) and CAS access (t_{CAC}). Both access periods must be calculated and the one with the least margin used. Also the number of data buffers should be kept to a minimum. Too many buffers would require either faster (more expensive) DRAMs, or a reduction in the performance of the CPU (by adding wait states).

RAS Access Margin

3TCLCL - 8207 TCLRSL max @ 150 pF - DRAM tRAC
- 74S240 propagation delay max @ 50 pF - 80286 t8 ≤ 0

$$187.5 \text{ ns} - 35 \text{ ns} - 120 \text{ ns} - 7 \text{ ns} - 10 \text{ ns} = 15.5 \text{ ns}$$

CAS Access Margin

2TCLCL - 8207 TCLCSL max @ 150 pF - DRAM tCAAC
(or tCAC - 74S240 tph max @ 50 pF - 80286 t8) ≤ 0

$$125 \text{ ns} - 35 \text{ ns} - 60 \text{ ns} - 7 \text{ ns} - 10 \text{ ns} = 13 \text{ ns}$$

By solving each equation for tRAC and tCAC, the speed requirement of the RAM can be determined.

$$\text{DRAM tRAC} = 3 \text{ TCLCL} - 8207 \text{ TCLRSL} - 74\text{S}240 \text{ tph} - 80286 \text{ t8} = 135.5 \text{ ns}$$

$$\text{DRAM tCAC} = 2 \text{ TCLCL} - 8207 \text{ TCLCSL} - 74\text{S}240 \text{ tph} - 80286 \text{ t8} = 73 \text{ ns}$$

NOTES:

1. Not specified. Assume no delay for worst case analysis.
2. STTL derated by 0.05 ns/pF.

So any DRAM that has a RAS access period less than 135 ns, a CAS access period less than 73 ns, and meets all requirements in the DRAM Interface Timing (Table 15, 16—8207 Data Sheet), will work.

Write Data Setup and Hold Margin

Write data from the processor must be valid when the 8207 issues WE to meet the DRAM specification tDS and then held to meet the tDH requirement. Some write cycles will be byte writes and the information to determine which byte is decoded from A0 and BHE/. Since the 80286's address bus is pipelined, these two signals can change before the RAM cycle starts, hence they must be latched by LEN. PSEN is used in the WE term to shorten the WE pulse. Its use is not essential.

Data must be set up to the falling edge of WE, since WE occurs after CAS. The 2 clocks between valid write data and WE going active (at the RAM's) minus propagation delays determines the margin.

$$2 \text{ TCLCL} - 80286 \text{ t14 (max)} @ 100 \text{ pF} - 74\text{S}240 \text{ tph} + 8207 \text{ TCLW (min)}^1 + 74\text{S}10 \text{ tph} @ 192 \text{ pF}^2 - \text{DRAM tDS} = 0$$

$$125 \text{ ns} - 50 \text{ ns} - 7 \text{ ns} + 0 \text{ ns} + 14 \text{ ns} - 0 \text{ ns} = 82 \text{ ns}$$

The timing of the 8207's acknowledge is such that data will be kept valid by the 80286, for more than two clocks after WE goes active. This easily meets all RAM tDH specifications.

SUMMARY

The 8207 complements the 80286's performance and high integration with its own performance, integration and ease of use. No critical timings or logic design has been left to the designer. The 80286/8207 combination allows users to realize maximum performance from their simpler design.